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See application file for complete search history.

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(57) **ABSTRACT**

A polymer capable of increasing alkali solubility under the action of acid, as a base resin is blended with a polymer comprising recurring units derived from a styrene having 1,1,1,3,3,3-hexafluoro-2-propanol as a polymeric additive to formulate a resist composition. The photoresist film formed using the resist composition is effective for minimizing outgassing therefrom during the EUV lithography, reducing LWR after development, and suppressing formation of blob defects after development because of its hydrophilic surface.

7 Claims, No Drawings